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Serial Number: 09/808750

Filing Date: March 15, 2001

DEVICE AND METHOD TO REDUCE WORDLINE RC TIME CONSTANT IN SEMICONDUCTOR MEMORY DEVICES

REMARKS

Applicant has carefully reviewed and considered the Office Action mailed on June 25, 2003, and the references cited therewith.

Claims 1, 5, 8, 15, 19, 26, 30, 37, 42, 45, and 49 are amended, no claims are canceled, and no claims are added; as a result, claims 1-54 are now pending in this application.

§103 Rejection of the Claims

Claims 1-54 were rejected under 35 USC § 103(a) as being unpatentable over Tanoi (U.S. Patent No. 5,708,621).

The pending office action states that Tanoi discloses a memory array including "a strapping line (118 in fig. 16) of lower resistance than the wordlines coupled to a single wordline wherein the strapping line bypasses a portion of the single wordline."

Applicant respectfully maintains that Tanoi does not disclose at least two channels connecting a strapping line to a first and second end of a portion of a **single** wordline as argued in previous responses. Further, Applicant respectfully maintains that Tanoi does not disclose a strapping wherein a width of the strapping line is greater than a width of the wordlines as argued in previous responses. However in the interest of moving the application forward towards allowance, Applicant has amended the claims to further distinguish the present claims from Tanoi.

Tanoi appears to show a single, continuous low resistance line 118 coupled to a single memory array 106. However, all embodiments of low resistance lines in Tanoi appears to be attached to wordlines at either a first end, or a second end of wordlines. Tanoi does not show a strapping line coupled to a single wordline that bypasses a portion in a middle region between a first and second end of the single wordline. Tanoi also does not show a plurality of separate strapping lines wherein the strapping lines bypass a plurality of separate portions of a single wordline.

In contrast, claims 1, 8, 15, 26, 30, 37, 45, and 49 as amended include a strapping line coupled to a single wordline that bypasses a portion in a middle region between a first and second end of the single wordline. Further in contrast, claims 5 and 19 as amended include a plurality of separate strapping lines wherein the strapping lines bypass a plurality of separate

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portions of a single wordline. Support for these embodiments can be found in the present specification on page 8, lines 21-28.

Further in contrast, claim 42 includes activating a first wordline in a **first memory array**, and activating a second wordline in a **second memory array**, wherein a signal used for activating the second wordline bypasses the first wordline through a strapping device of lower resistance than the first wordline. Applicant is unable to find any embodiments of Tanoi referring to multiple memory arrays.

Because, as stated by the Examiner, the single Tanoi reference, does not show every element of Applicant's independent claims as amended, a 35 USC § 103(a) rejection is not supported by the references. Reconsideration and withdrawal of the rejection is respectfully requested with respect to Applicant's independent claims 1, 5, 8, 15, 19, 26, 30, 37, 42, 45, and 49. Additionally, reconsideration and withdrawal of the rejection is respectfully requested with respect to the remaining claims that depend therefrom as depending on allowable base claims.

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CONCLUSION

Applicant respectfully submits that the claims are in condition for allowance and